Image may be representation.
See specs for product details.

SIR412DP-T1-GE3

Hersteller-Teilenummer:	SIR412DP-T1-GE3
Hersteller / Marke:	Electro-Films (EFI) / Vishay
Teil der Beschreibung:	MOSFET N-CH 25V 20A PPAK SO-8
Datenblätter:	SIR412DP-T1-GE3.pdf
RoHs Status:	Bleifrei / RoHS-konform
Lagerzustand:	New original, 819423 pcs Stock Available.
Liefern von:	Hong Kong
Versandweg:	DHL/Fedex/TNT/UPS/EMS

Spezifikationen

Teilenummer	SIR412DP-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 25V 20A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	819423 pcs Stock
detaillierte Beschreibung	N-Channel 25V 20A (Tc) 3.9W (Ta), 15.6W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	3.9W (Ta), 15.6W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	25V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	20A (Tc)
Rds On (Max) @ Id, Vgs	12 mOhm @ 10A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	16nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	600pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SIR412DP-T1-GE3TR

SIR412DP-T1-GE3 ist neu im Original, Suche SIR412DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIR412DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIR412DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

SIR414DP
VB
SIR414DP VB

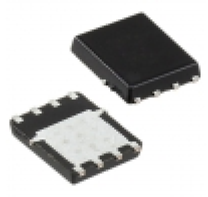
SIR414DP-T1-GE3
Electro-Films (EFI) / Vishay
MOSFET N-CH 40V 50A PPAK SO-8

SiR412DP-T1-E3
Vishay Precision Group
SiR412DP-T1-E3 VISHAY

SiR410DP-T1-E3
VISHAY
SiR410DP-T1-E3 VISHAY

SiR414DP-T1-E3
VISHAY
SiR414DP-T1-E3 VISHAY

SiR412DP
Vishay Precision Group
SiR412DP VISHAY



SIR414DP-T1-GE3
Vishay / Siliconix
MOSFET N-CH 40V 50A PPAK SO-8

SIR412DP-T1-GE3
Vishay / Siliconix
MOSFET N-CH 25V 20A PPAK SO-8

heiße Teile

Mehr

- SIR172DP-T1-E3
- SIR172DP-T1-GE3
- SIR172DP-T1-GE3
- SIR330DP-T1-GE3
- SIR330DP-T1-GE3
- SIR402DP-T1-GE3
- SIR402DP-T1-GE3
- SIR403EDP-T1-GE3
- SIR403EDP-T1-GE3
- SIR404DP
- SiR404DP-T1-GE3
- SIR404DP-T1-GE3
- SIR404DP-T1-GE3
- SIR406DP
- SIR406DP-T1-E3
- SIR406DP-T1-GE3
- SIR406DP-T1-GE3
- SIR406DP-T1-GE3-S
- SIR408DP-T1-GE3
- SIR408DP-T1-GE3
- SIR410DP-T1-E3
- SIR410DP-T1-GE3
- SIR410DP-T1-GE3
- SIR412DP
- SIR412DP-T1-E3
- SIR412DP-T1-GE3
- SIR414DP
- SIR414DP-T1-GE3
- SIR414DP-T1-GE3
- SIR416DP
- SIR416DP-T1-E3
- SIR416DP-T1-GE3
- SIR416DP-T1-GE3
- SIR418DP-T1-E3
- SIR418DP-T1-GE3
- SIR418DP-T1-GE3
- SIR422DP-T1-E3
- SIR422DP-T1-GE3
- SIR422DP-T1-GE3
- SIR424DP-T1-GE3
- SIR424DP-T1-GE3
- SIR426DP-T1-GE3
- SIR426DP-T1-GE3
- SIR428DP
- SIR428DP-T1-E3
- SIR428DP-T1-GE3
- SIR432DP-T1-GE3
- SIR432DP-T1-GE3
- SIR436DP-T1-E3
- SIR436DP-T1-GE3

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